



75NM65-U2

Power MOSFET

75A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

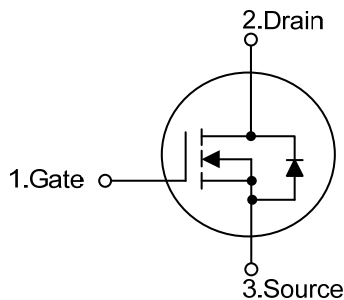
DESCRIPTION

The **UTC 75NM65-U2** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)} \leq 55 \text{ m}\Omega$ @ $V_{GS}=10\text{V}$, $I_D=18.75\text{A}$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

SYMBOL

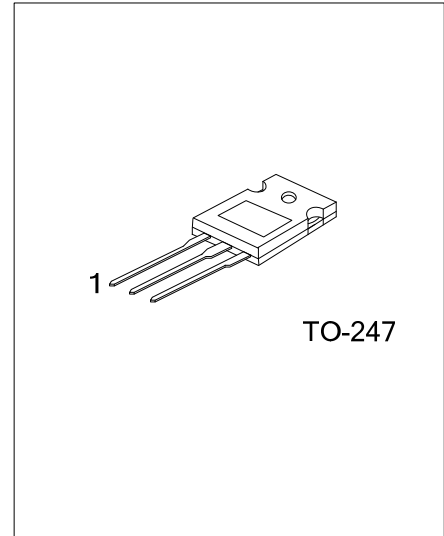


ORDERING INFORMATION

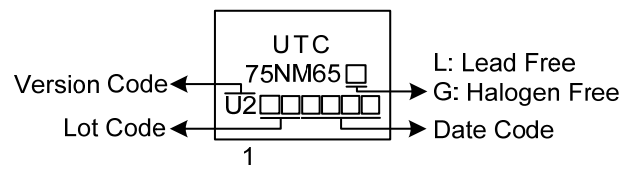
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
75NM65L-U2-T47-T	75NM65G-U2-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

75NM65G-U2-T47-T	(1)Packing Type (2)Package Type (3)Version Code (4)Green Package	(1) T: Tube (2) T47: TO-247 (3) Version U2 (4) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	75	A
	Pulsed (Note 2)	I_{DM}	225	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	1326	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	0.7	V/ns
Power Dissipation		P_D	250	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 100\text{mH}$, $I_{AS} = 5.1\text{A}$, $V_{DD} = 90\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 30\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	40	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	0.5	$^\circ\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

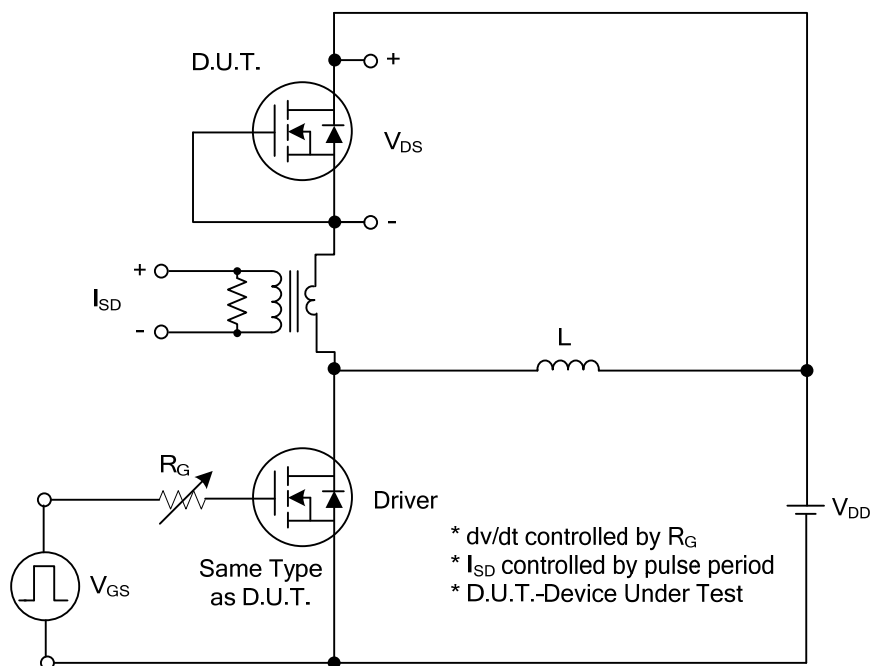
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	650			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =18.75A			55	mΩ
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =50V, f=1MHz		4490		pF
Output Capacitance	C _{OSS}			1866		pF
Reverse Transfer Capacitance	C _{RSS}			123		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q _G	V _{DS} =520V, V _{GS} =10V, I _D =75A (Note 1, 2)		235		nC
Gate-Source Charge	Q _{GS}			41		nC
Gate-Drain Charge	Q _{DD}			128		nC
Turn-On Delay Time	t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =75A, R _G =25Ω (Note 1, 2)		72		ns
Turn-On Rise Time	t _R			272		ns
Turn-Off Delay Time	t _{D(OFF)}			496		ns
Turn-Off Fall Time	t _F			131		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				75	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				225	A
Drain-Source Diode Forward Voltage	V _{SD}	I _S =75A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time	t _{rr}	I _S =30A, V _{GS} =0V,		664		nS
Body Diode Reverse Recovery Charge	Q _{rr}	dI _F /dt=100A/μs		14		μC

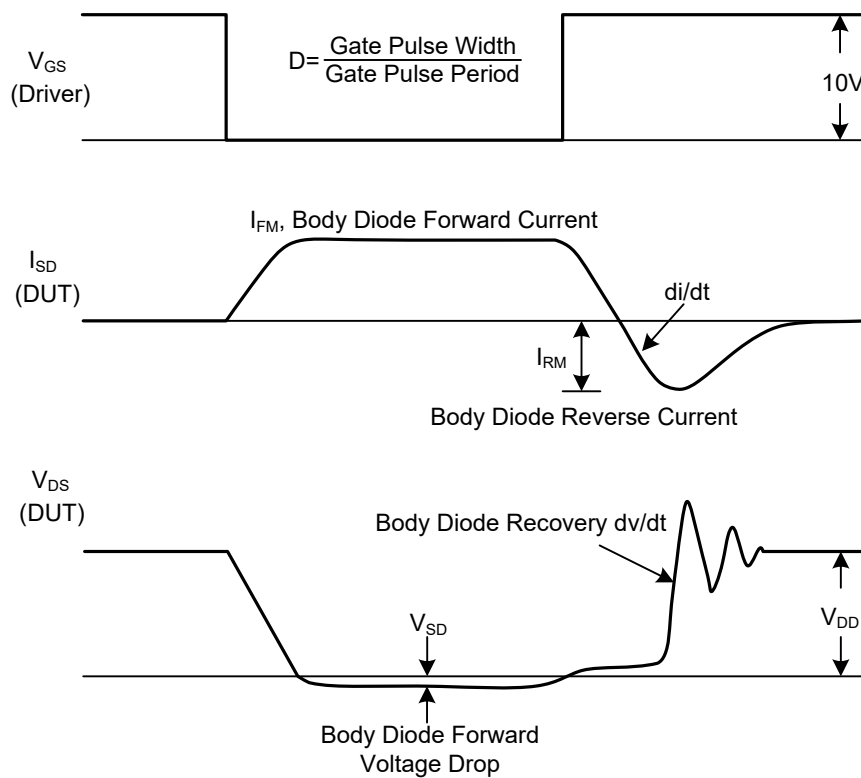
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

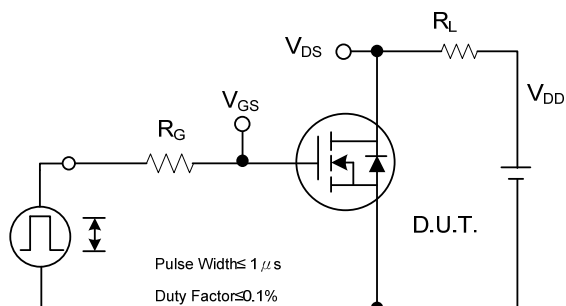


Peak Diode Recovery dv/dt Test Circuit

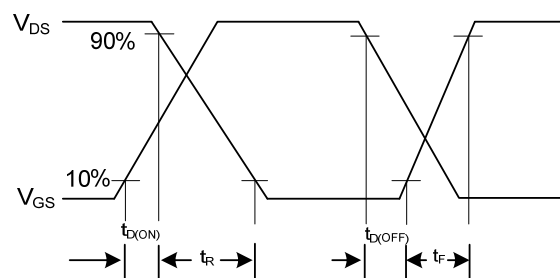


Peak Diode Recovery dv/dt Waveforms

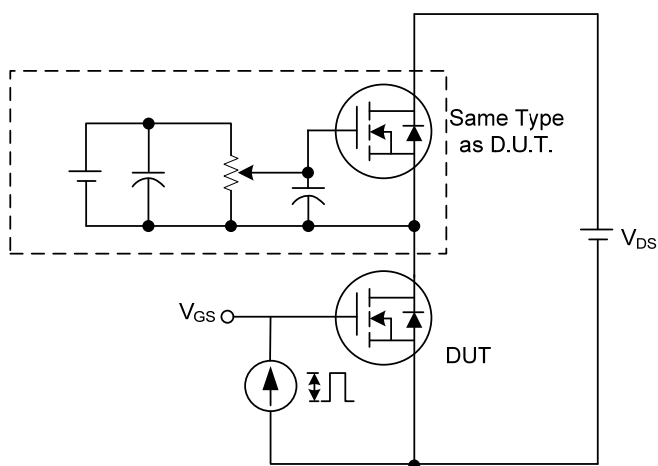
■ TEST CIRCUITS AND WAVEFORMS



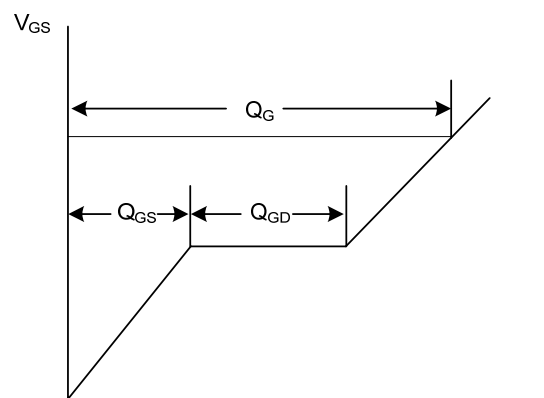
Switching Test Circuit



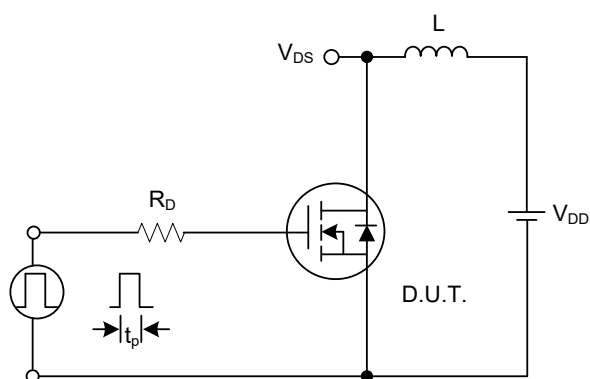
Switching Waveforms



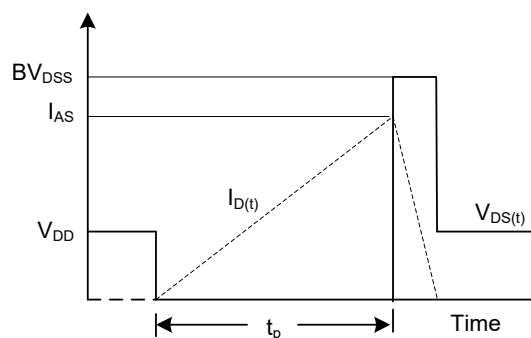
Gate Charge Test Circuit



Gate Charge Waveform

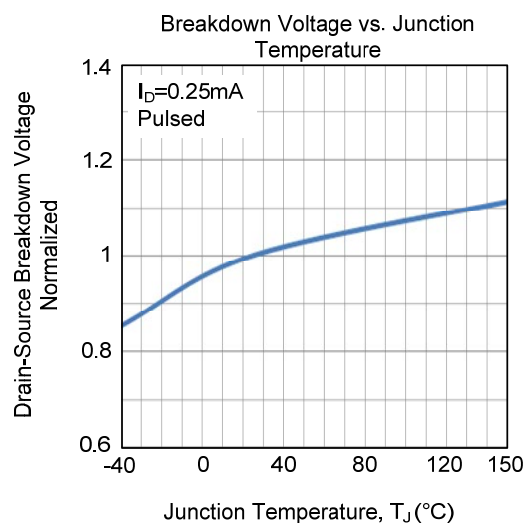
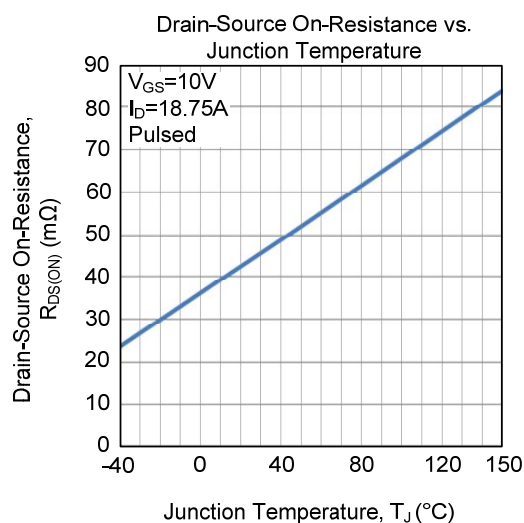
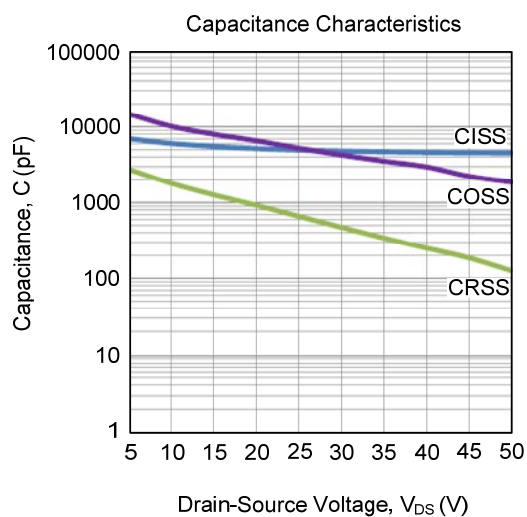
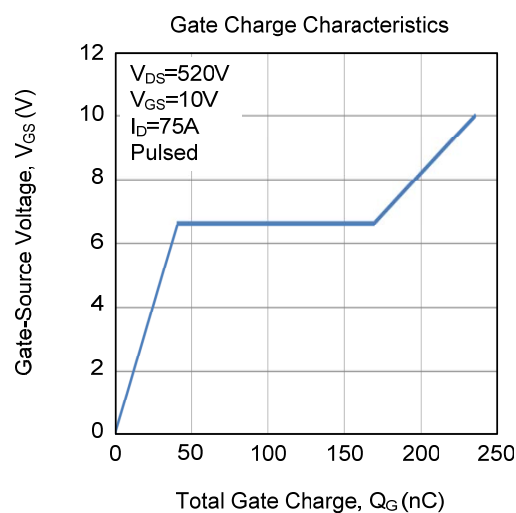
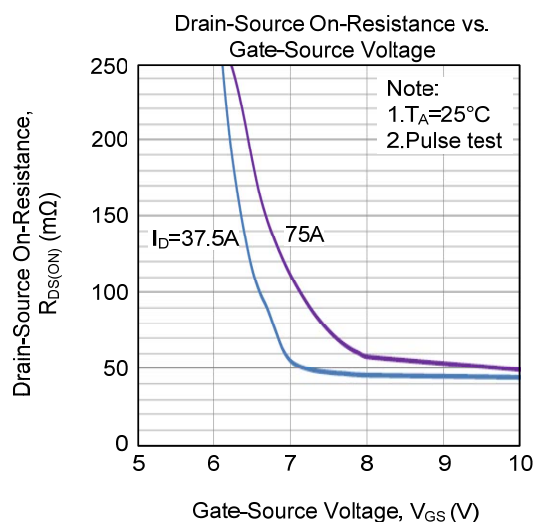
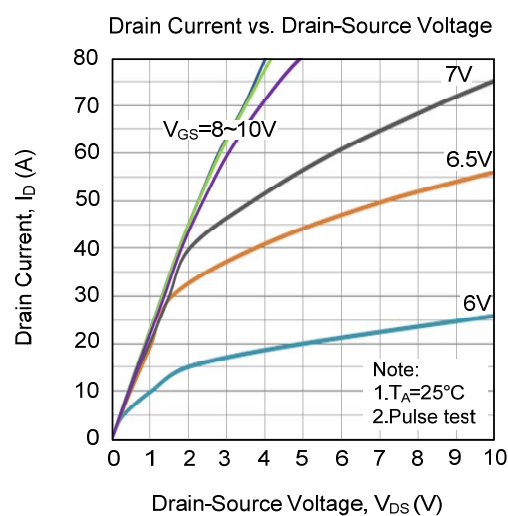


Unclamped Inductive Switching Test Circuit

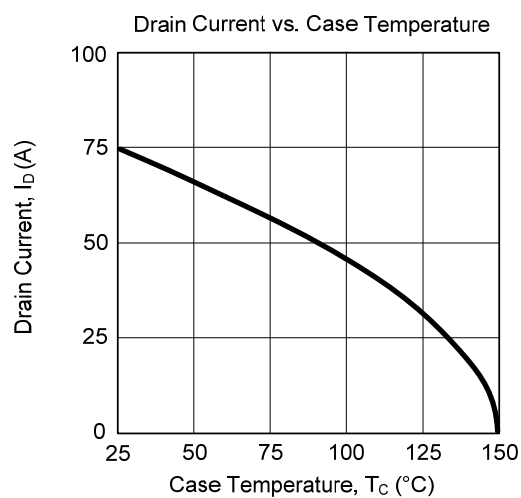
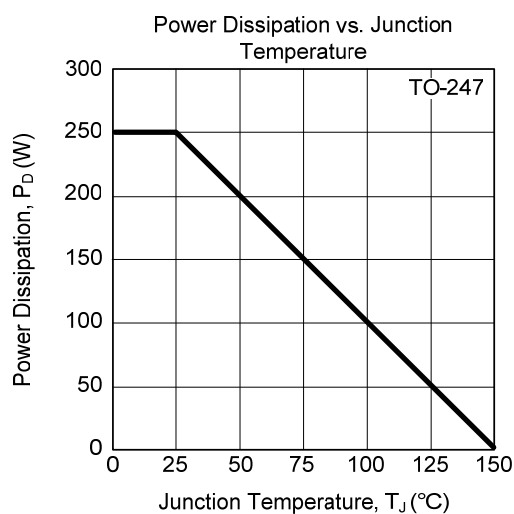
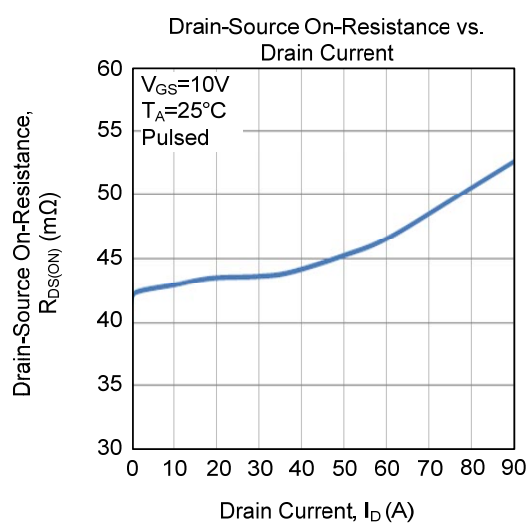
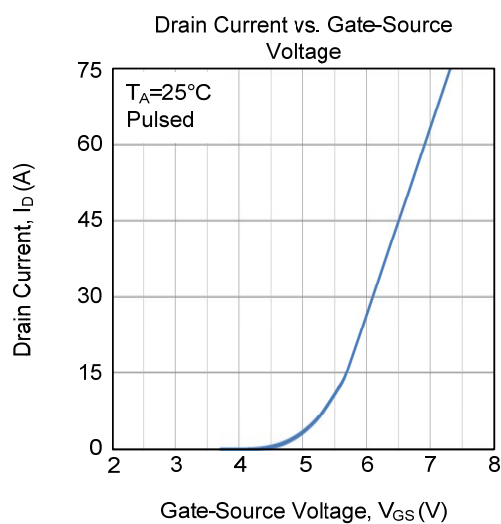
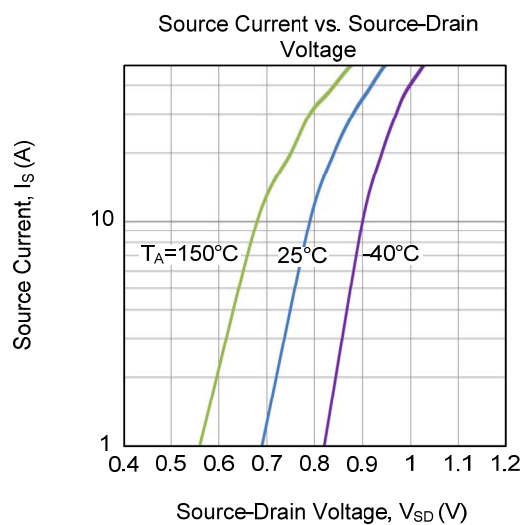
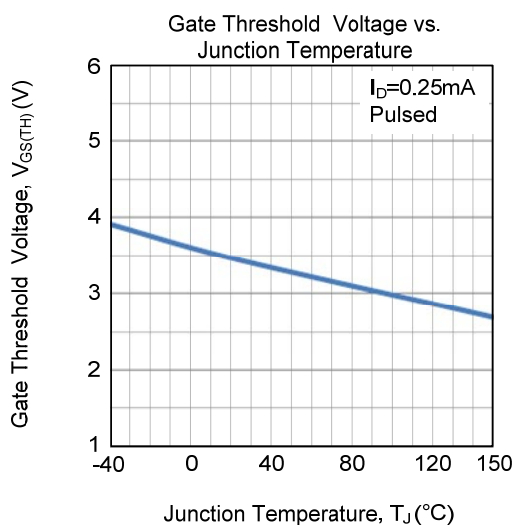


Unclamped Inductive Switching Waveforms

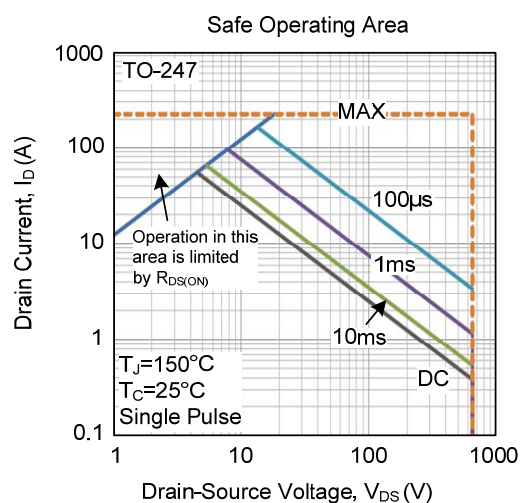
TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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